

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-18. (Cancelled)

19. (Previously Presented) A method for fabricating a circuit device comprising:
preparing a laminated sheet comprising a conductive film, an insulation resin formed on the surface of the conductive film, and a first conductive path layer formed on the surface of the insulation resin;
adhering and fixing a semiconductor element above the first conductive path layer;
providing sealing resin as an overcoat to the first conductive path layer and the semiconductor element;
forming a second conductive path layer by etching the conductive film into a predetermined pattern; and
forming an external electrode at predetermined points of the second conductive path layer.

20. (Previously Presented) The method of claim 19 wherein preparing the laminated sheet comprises:
forming a through hole in the insulation resin at predetermined points of the laminated sheet, and selectively exposing a rear surface of the conductive film;
providing a conductive plated film over surfaces of the through hole and the insulation resin; and
forming the first conductive path layer by etching the conductive plated film into a predetermined pattern.

21. (Previously Presented) The method of claim 19 wherein the conductive film and the conductive plated film comprise copper.

22. (Previously Presented) The method of claim 19 wherein the conductive plated film is formed to be thin, and the first conductive path layer is finely patterned.

23. (Previously Presented) The method of claim 19 wherein the conductive film is sufficiently thick to provide mechanical support until the insulation resin layer is provided on the conductive film.

24. (Previously Presented) The method of claim 19 wherein the conductive film is mechanically supported by the sealing resin after providing the sealing resin layer as an overcoat.

25. (Previously Presented) The method of claim 20 wherein the through holes are prepared by laser etching of the insulation resin.

26. (Previously Presented) The method of claim 25 wherein the laser etching utilizes a carbonic acid gas laser.

27. (Previously Presented) The method of claim 20 wherein the conductive plated film is formed on the surface of the through holes and the insulation resin by non-electrolytic plating and electrolytic plating of a conductive metal.

28. (Previously Presented) The method of claim 19 wherein predetermined points of the first conductive path layer are exposed and not covered by the sealing resin .

29. (Previously Presented) The method of claim 28 including forming a gold or silver plated layer at the exposed points of the first conductive path layer.

30. (Previously Presented) The method of claim 28 wherein the semiconductor element is adhered to and fixed on a sealing resin layer.

31. (Previously Presented) The method of claim 29 wherein electrodes of the semiconductor element and the gold or silver plated layer are connected to each other by bonding wires.

32. (Previously Presented) The method of claim 19 wherein the sealing resin layer is formed by a transfer mold process.

33. (Previously Presented) The method of claim 19 wherein the conductive film is thinned by etching the entire surface evenly without a mask.

34. (Previously Presented) The method of claim 19 wherein almost all of the second conductive path layer is covered by an overcoating resin.

35. (Previously Presented) The method of claim 19 wherein external electrodes have solder adhered thereto by screen printing of solder, and are formed by being heated and dissolved.

36. (Previously Presented) The method of claim 19 wherein external electrodes are formed by reflowing of solder.

37. (Previously Presented) The method of claim 19 wherein external electrodes are formed with the surface thereof plated with gold or palladium by etching the conductive layer into a predetermined pattern.

38. (Previously Presented) The method of claim 19 wherein the first conductive path layer comprises a plated film.

39. (Currently amended) The method of claim 19 wherein forming the second conductive path layer is performed after making the conductive film thin by etching the entire surface thereof.